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* Design Problem, ee114/214A- 2012
* Please fill in the specification achieved by your circuit
* before your submit the netlist.
         *********************
* The specifications that this script achieves are:
* sunetid = rohitpid, samfok
* Power = 1.5667 mW
* Gain = 20.148 K
* BandWidth = 90.041 MHz
*************************
** Including the model file
.include /usr/class/ee114/hspice/ee114 hspice.sp
* Defining Top level circuit parameters
.param Cin = 100f
.param CL = 500f
.param RL = 10K
* defining the supply voltages
vdd vdd 0 2.5
vss vss 0 -2.5
* Defining the input current source
** For ac simulation uncomment the following 2 lines**
 Iina
               iina
                       vdd
                                       0.5
                               ac
 Iinb
               bbv
                       iinb
                               ac
                                       0.5
** For transient simulation uncomment the following 2 lines**
*Iina
                       vdd
                               sin(0 0.5u 1e6)
               iina
*Iinb
               vdd
                       iinb
                               sin(0 0.5u 1e6)
* Defining Input capacitance
        vdd
               iina 'Cin'
Cina
Cinb
        vdd
               iinb 'Cin'
* Defining the differential load
                                       'RL'
RL
        vouta
                       voutb
CL
        vouta
                       voutb
*** Your Trans-impedance Amplifier here ***
**nmos***
*name drain gate source bulk type parameters*
    node_1a 0 iina vss nmos114 w=14.2u l=1u
    node_1b 0 iinb vss nmos114 w=14.2u l=1u
    node_2a node_1a ibias2 vss nmos114 w=6.8u l=1u
M2a
    node 2b node 1b ibias2 vss nmos114 w=6.8u l=1u
M2b
    vdd node 2a vouta vss nmos114 w=40.2u l=1u
    vdd node 2b voutb vss nmos114 w=40.2u l=1u
M3b
**pmos***
*name drain gate source bulk type parameters*
ML1a node_1a node_1a vdd vdd pmos114 w=2.4u l=1u
ML1b node_1b node_1b vdd vdd pmos114 w=2.4u l=1u
ML2a node_2a node_2a vdd vdd pmos114 w=2.8u l=1u
ML2b node_2b node_2b vdd vdd pmos114 w=2.8u l=1u
*** Your Bias Circuitry here ***
**nmos***
*name drain gate source bulk type parameters*
Mbiasla iina nbias vss vss nmosl14 w=2.2u l=2u
Mbias1b iinb nbias vss vss nmos114 w=2.2u l=2u
```

.end

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Mbias2a ibias2 nbias vss vss nmos114 w=2.2u l=2u
Mbias2b ibias2 nbias vss vss nmos114 w=2.2u l=2u
Mbias3a vouta nbias vss vss nmos114 w=5.6u l=2u
Mbias3b voutb nbias vss vss nmos114 w=5.6u l=2u
*** nmos
*** drain gate source bulk mostype w_value l_value
Mu nbias nbias vx vss nmos114 w=2u l=1u
Ml vx nbias vss vss nmos114 w=2u l=1u
*Resistors
R vdd nbias 140k
* defining the analysis
.option post brief nomod
** For ac simulation uncomment the following line**
.ac dec 100 100 10g
.measure ac gainmax max vdb(vouta)
.measure ac f3db when vdb(vouta)='gainmax-3'
** For transient simulation uncomment the following line **
*.tran 0.01u 4u
```